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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p250-vq100

Microsemi

Power Matters.™

1 – ProASIC3 Device Family Overview

General Description

ProASIC3, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC^PLUS® family. Nonvolatile flash technology gives ProASIC3 devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3 is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3 devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The A3P015 and A3P030 devices have no PLL or RAM support. ProASIC3 devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

ProASIC3 devices support the ARM Cortex-M1 processor. The ARM-enabled devices have Microsemi ordering numbers that begin with M1A3P (Cortex-M1) and do not support AES decryption.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3 devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3 family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3 family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3 devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3 devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3 devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for intellectual property and configuration data. In addition, all FlashROM data in ProASIC3 devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3 devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3 devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

ARM-enabled ProASIC3 devices do not support user-controlled AES security mechanisms. Since the ARM core must be protected at all times, AES encryption is always on for the core logic, so bitstreams are always encrypted. There is no user access to encryption for the FlashROM programming data.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3 family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3 family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks.

Table 2-15 • **Different Components Contributing to the Static Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: **For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = P_{DC1} + N_{INPUTS}* P_{DC2} + N_{OUTPUTS}* P_{DC3}$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (P_{AC1} + N_{SPINE}*P_{AC2} + N_{ROW}*P_{AC3} + N_{S-CELL}* P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.
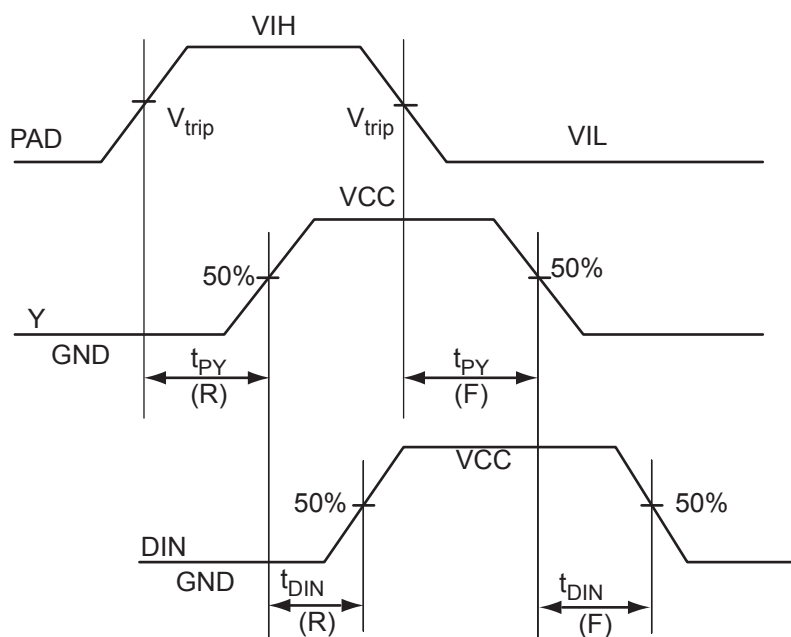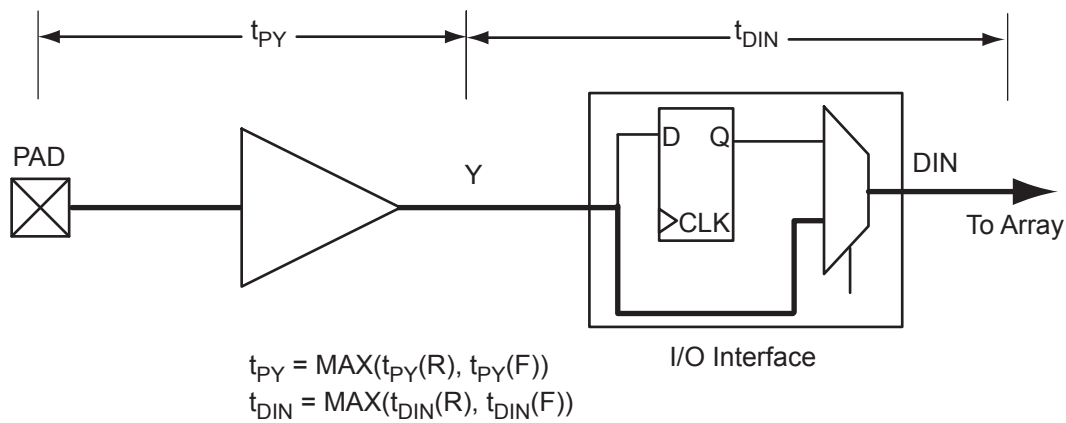
$t_{PY} = MAX(t_{PY}(R), t_{PY}(F))$
$t_{DIN} = MAX(t_{DIN}(R), t_{DIN}(F))$

Figure 2-4 • **Input Buffer Timing Model and Delays (Example)**

Table 2-29 • **I/O Output Buffer Maximum Resistances** [1]
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	$R_{PULL-DOWN}$ (Ω)[2]	$R_{PULL-UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range[4]	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*

2. *$R_{(PULL-DOWN-MAX)}$ = (VOLspec) / IOLspec*

3. *$R_{(PULL-UP-MAX)}$ = (VCCImax – VOHspec) / IOHspec*

4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*

Table 2-44 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	9.68	0.04	1.00	0.43	9.86	8.42	2.28	2.21	12.09	10.66	ns
	−1	0.56	8.23	0.04	0.85	0.36	8.39	7.17	1.94	1.88	10.29	9.07	ns
	−2	0.49	7.23	0.03	0.75	0.32	7.36	6.29	1.70	1.65	9.03	7.96	ns
4 mA	Std.	0.66	9.68	0.04	1.00	0.43	9.86	8.42	2.28	2.21	12.09	10.66	ns
	−1	0.56	8.23	0.04	0.85	0.36	8.39	7.17	1.94	1.88	10.29	9.07	ns
	−2	0.49	7.23	0.03	0.75	0.32	7.36	6.29	1.70	1.65	9.03	7.96	ns
6 mA	Std.	0.66	6.70	0.04	1.00	0.43	6.82	5.89	2.58	2.74	9.06	8.12	ns
	−1	0.56	5.70	0.04	0.85	0.36	5.80	5.01	2.20	2.33	7.71	6.91	ns
	−2	0.49	5.00	0.03	0.75	0.32	5.10	4.40	1.93	2.05	6.76	6.06	ns
8 mA	Std.	0.66	6.70	0.04	1.00	0.43	6.82	5.89	2.58	2.74	9.06	8.12	ns
	−1	0.56	5.70	0.04	0.85	0.36	5.80	5.01	2.20	2.33	7.71	6.91	ns
	−2	0.49	5.00	0.03	0.75	0.32	5.10	4.40	1.93	2.05	6.76	6.06	ns
12 mA	Std.	0.66	5.05	0.04	1.00	0.43	5.14	4.51	2.79	3.08	7.38	6.75	ns
	−1	0.56	4.29	0.04	0.85	0.36	4.37	3.84	2.38	2.62	6.28	5.74	ns
	−2	0.49	3.77	0.03	0.75	0.32	3.84	3.37	2.09	2.30	5.51	5.04	ns
16 mA	Std.	0.66	5.05	0.04	1.00	0.43	5.14	4.51	2.79	3.08	7.38	6.75	ns
	−1	0.56	4.29	0.04	0.85	0.36	4.37	3.84	2.38	2.62	6.28	5.74	ns
	−2	0.49	3.77	0.03	0.75	0.32	3.84	3.37	2.09	2.30	5.51	5.04	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-45 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	−1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	−2	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
4 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	−1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	−2	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
6 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	−1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns
	−2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
8 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	−1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns

Table 2-73 • **1.8 V LVCMOS Low Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	t$_{ZLS}$	t$_{ZHS}$	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	−1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	−2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	−1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	−2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	−1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	−2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	−1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	−2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-74 • **1.8 V LVCMOS High Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	−1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	−2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	−1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	−2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-83 • **1.5 V LVCMOS Low Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	t$_{ZLS}$	t$_{ZHS}$	Units
2 mA	Std.	0.66	12.08	0.04	1.42	0.43	12.01	12.08	2.72	2.43	14.24	14.31	ns
	−1	0.56	10.27	0.04	1.21	0.36	10.21	10.27	2.31	2.06	12.12	12.18	ns
	−2	0.49	9.02	0.03	1.06	0.32	8.97	9.02	2.03	1.81	10.64	10.69	ns
4 mA	Std.	0.66	9.28	0.04	1.42	0.43	9.45	8.91	3.04	3.00	11.69	11.15	ns
	−1	0.56	7.89	0.04	1.21	0.36	8.04	7.58	2.58	2.55	9.94	9.49	ns
	−2	0.49	6.93	0.03	1.06	0.32	7.06	6.66	2.27	2.24	8.73	8.33	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-84 • **1.5 V LVCMOS High Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	Units
2 mA	Std.	0.66	7.65	0.04	1.42	0.43	6.31	7.65	2.45	2.45	ns
	−1	0.56	6.50	0.04	1.21	0.36	5.37	6.50	2.08	2.08	ns
	−2	0.49	5.71	0.03	1.06	0.32	4.71	5.71	1.83	1.83	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-85 • **1.5 V LVCMOS Low Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	Units
2 mA	Std.	0.66	12.33	0.04	1.42	0.43	11.79	12.33	2.45	2.32	ns
	−1	0.56	10.49	0.04	1.21	0.36	10.03	10.49	2.08	1.98	ns
	−2	0.49	9.21	0.03	1.06	0.32	8.81	9.21	1.83	1.73	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-111 • **A3P250 Global Resource**
  Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	−2		−1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_RCKL	Input Low Delay for Global Clock	0.80	1.01	0.91	1.15	1.07	1.36	ns
t_RCKH	Input High Delay for Global Clock	0.78	1.04	0.89	1.18	1.04	1.39	ns
t_RCKMPWH	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t_RCKMPWL	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_RCKSW	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*

2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*

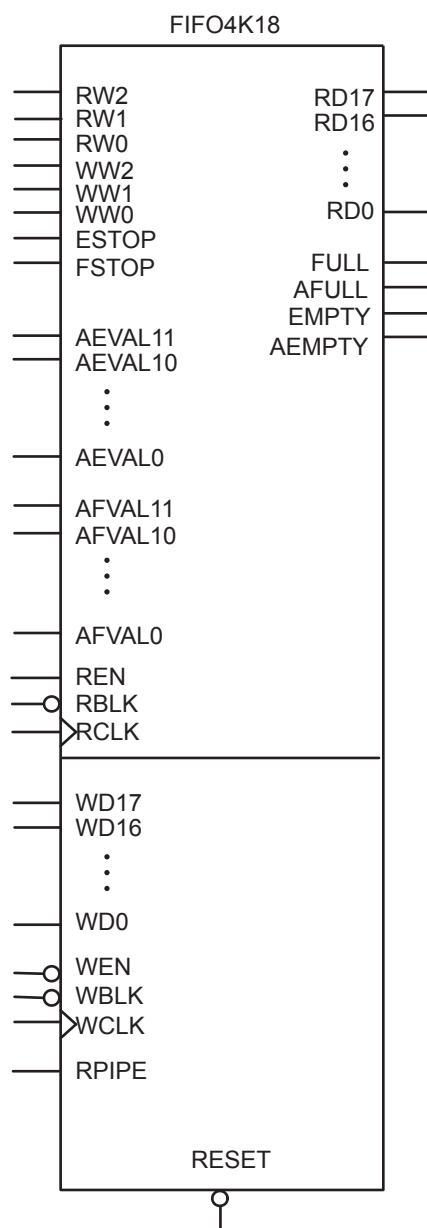3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-112 • **A3P400 Global Resource**
  Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	−2		−1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_RCKL	Input Low Delay for Global Clock	0.87	1.09	0.99	1.24	1.17	1.46	ns
t_RCKH	Input High Delay for Global Clock	0.86	1.11	0.98	1.27	1.15	1.49	ns
t_RCKMPWH	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t_RCKMPWL	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_RCKSW	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*

2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*

3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

FIFO

Figure 2-36 • **FIFO Model**

Table 2-123 • **A3P250 FIFO 4k×1 (continued)**
Worst Commercial-Case Conditions: T$_J$ = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t$_{RSTAF}$	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t$_{RSTBQ}$	RESET Low to Data Out Low on DO (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
t$_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
t$_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
t$_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t$_{CYC}$	Clock Cycle Time	3.23	3.68	4.32	ns
F$_{MAX}$	Maximum Frequency	310	272	231	MHz

Embedded FlashROM Characteristics
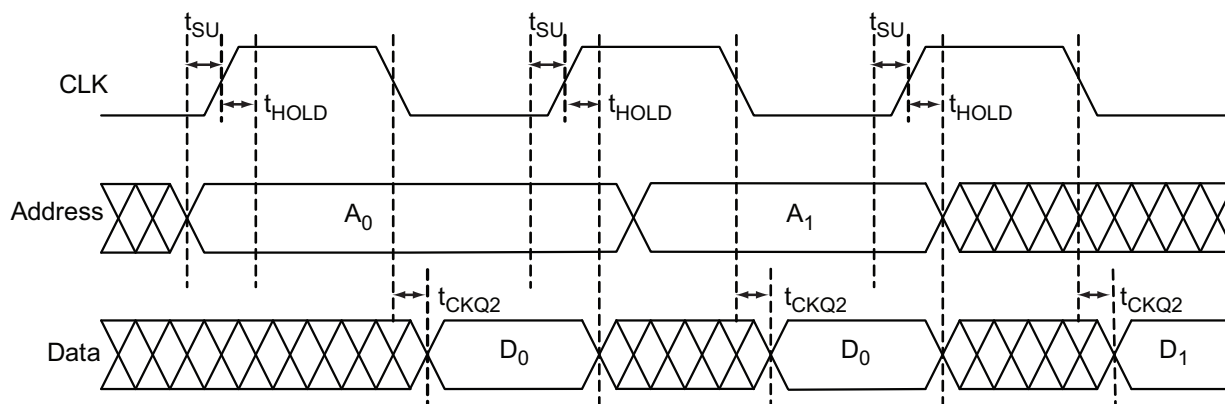
Figure 2-44 • **Timing Diagram**

Timing Characteristics

Table 2-124 • **Embedded FlashROM Access Time**

Parameter	Description	–2	–1	Std.	Units
t$_{SU}$	Address Setup Time	0.53	0.61	0.71	ns
t$_{HOLD}$	Address Hold Time	0.00	0.00	0.00	ns
t$_{CK2Q}$	Clock to Out	21.42	24.40	28.68	ns
F$_{MAX}$	Maximum Clock Frequency	15	15	15	MHz

mode is not used in the design, the FF pin is available as a regular I/O. For IGLOOe, ProASIC3EL, and RT ProASIC3 only, the FF pin can be configured as a Schmitt trigger input.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK   **Test Clock**

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 1 for more information.

Table 1 • **Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance
3.3 V	200 Ω –1 kΩ
2.5 V	200 Ω –1 kΩ
1.8 V	500 Ω –1 kΩ
1.5 V	500 Ω –1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on the JTAG chain*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin is pulled down.*

TDI   **Test Data Input**

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO   **Test Data Output**

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS   **Test Mode Select**
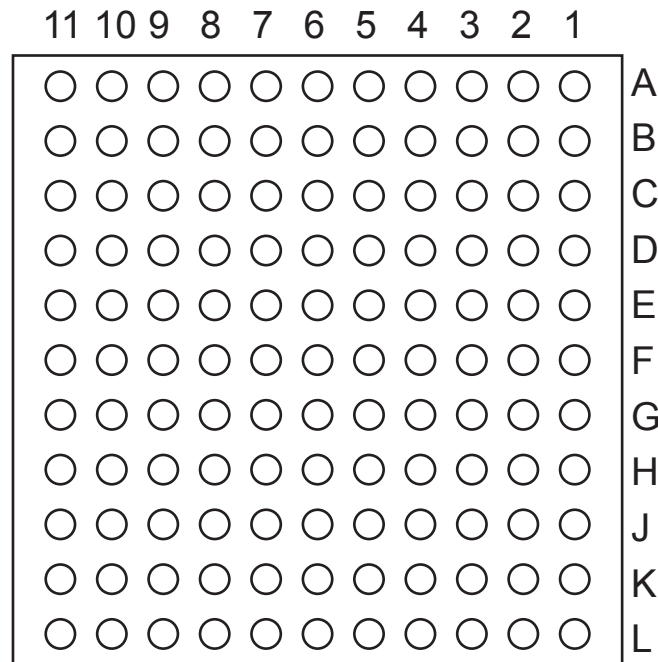
The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST   **Boundary Scan Reset Pin**

The TRST pin functions as an active low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 1 and must satisfy the parallel resistance value requirement. The values in Table 1 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

CS121 – Bottom View

```
      11 10 9  8  7  6  5  4  3  2  1
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  A
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  B
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  C
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  D
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  E
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  F
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  G
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  H
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  J
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  K
     ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○  L
```

Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

TQ144	
Pin Number	**A3P060 Function**
109	NC
110	NC
111	GBA1/IO24RSB0
112	GBA0/IO23RSB0
113	GBB1/IO22RSB0
114	GBB0/IO21RSB0
115	GBC1/IO20RSB0
116	GBC0/IO19RSB0
117	VCCIB0
118	GND
119	VCC
120	IO18RSB0
121	IO17RSB0
122	IO16RSB0
123	IO15RSB0
124	IO14RSB0
125	IO13RSB0
126	IO12RSB0
127	IO11RSB0
128	NC
129	IO10RSB0
130	IO09RSB0
131	IO08RSB0
132	GAC1/IO07RSB0
133	GAC0/IO06RSB0
134	NC
135	GND
136	NC
137	GAB1/IO05RSB0
138	GAB0/IO04RSB0
139	GAA1/IO03RSB0
140	GAA0/IO02RSB0
141	IO01RSB0
142	IO00RSB0
143	GNDQ
144	VMV0

PQ208 – Top View

208-Pin PQFP
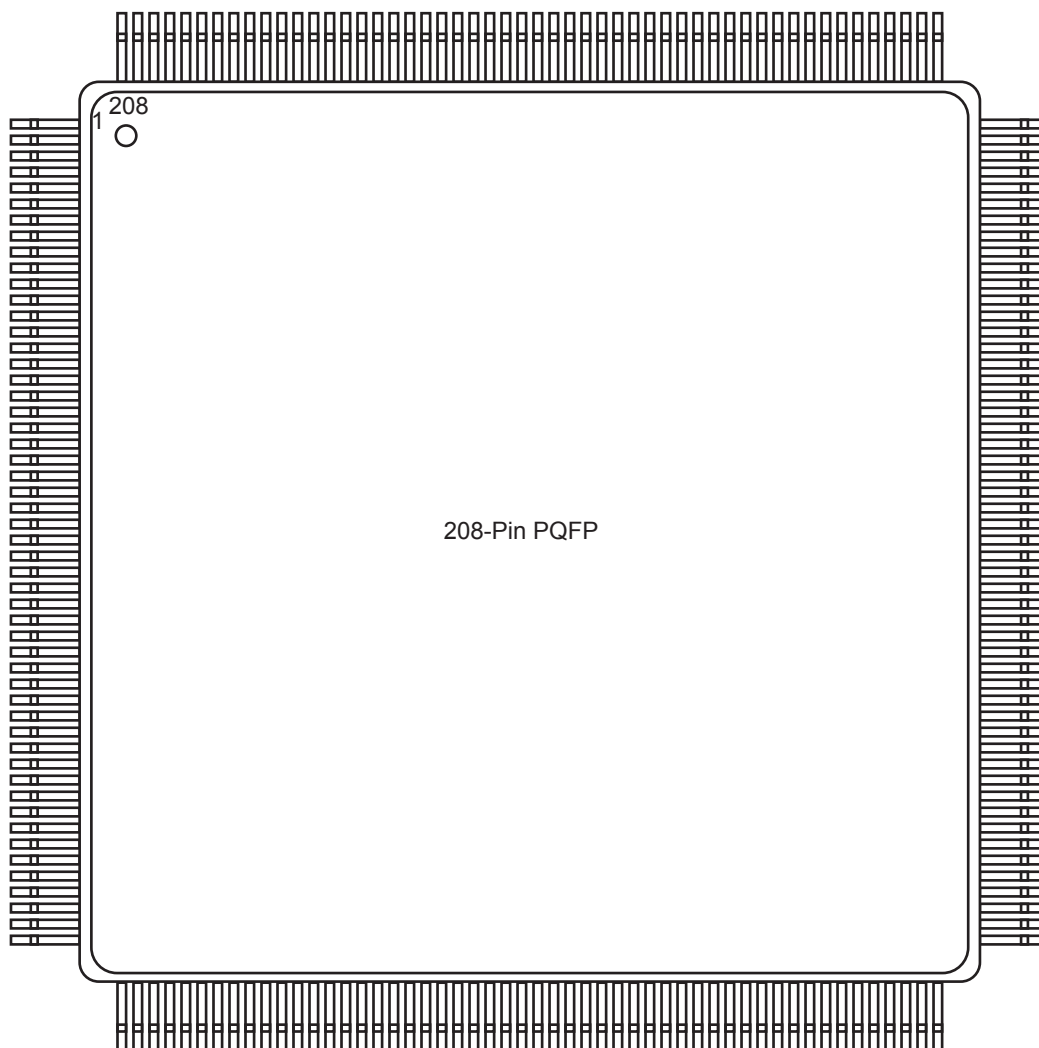
Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

PQ208	
Pin Number	A3P125 Function
109	TRST
110	VJTAG
111	GDA0/IO66RSB0
112	GDA1/IO65RSB0
113	GDB0/IO64RSB0
114	GDB1/IO63RSB0
115	GDC0/IO62RSB0
116	GDC1/IO61RSB0
117	NC
118	NC
119	NC
120	NC
121	NC
122	GND
123	VCCIB0
124	NC
125	NC
126	VCC
127	IO60RSB0
128	GCC2/IO59RSB0
129	GCB2/IO58RSB0
130	GND
131	GCA2/IO57RSB0
132	GCA0/IO56RSB0
133	GCA1/IO55RSB0
134	GCB0/IO54RSB0
135	GCB1/IO53RSB0
136	GCC0/IO52RSB0
137	GCC1/IO51RSB0
138	IO50RSB0
139	IO49RSB0
140	VCCIB0
141	GND
142	VCC
143	IO48RSB0
144	IO47RSB0

PQ208	
Pin Number	A3P125 Function
145	IO46RSB0
146	NC
147	NC
148	NC
149	GBC2/IO45RSB0
150	IO44RSB0
151	GBB2/IO43RSB0
152	IO42RSB0
153	GBA2/IO41RSB0
154	VMV0
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

PQ208	
Pin Number	A3P125 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

PQ208		PQ208		PQ208	
Pin Number	**A3P400 Function**	**Pin Number**	**A3P400 Function**	**Pin Number**	**A3P400 Function**
1	GND	37	IO141PSB3	73	IO112RSB2
2	GAA2/IO155UDB3	38	IO140PDB3	74	IO111RSB2
3	IO155VDB3	39	IO140NDB3	75	IO110RSB2
4	GAB2/IO154UDB3	40	VCCIB3	76	IO109RSB2
5	IO154VDB3	41	GND	77	IO108RSB2
6	GAC2/IO153UDB3	42	IO138PDB3	78	IO107RSB2
7	IO153VDB3	43	IO138NDB3	79	IO106RSB2
8	IO152UDB3	44	GEC1/IO137PDB3	80	IO104RSB2
9	IO152VDB3	45	GEC0/IO137NDB3	81	GND
10	IO151UDB3	46	GEB1/IO136PDB3	82	IO102RSB2
11	IO151VDB3	47	GEB0/IO136NDB3	83	IO101RSB2
12	IO150PDB3	48	GEA1/IO135PDB3	84	IO100RSB2
13	IO150NDB3	49	GEA0/IO135NDB3	85	IO99RSB2
14	IO149PDB3	50	VMV3	86	IO98RSB2
15	IO149NDB3	51	GNDQ	87	IO97RSB2
16	VCC	52	GND	88	VCC
17	GND	53	VMV2	89	VCCIB2
18	VCCIB3	54	NC	90	IO94RSB2
19	IO148PDB3	55	GEA2/IO134RSB2	91	IO92RSB2
20	IO148NDB3	56	GEB2/IO133RSB2	92	IO90RSB2
21	GFC1/IO147PDB3	57	GEC2/IO132RSB2	93	IO88RSB2
22	GFC0/IO147NDB3	58	IO131RSB2	94	IO86RSB2
23	GFB1/IO146PDB3	59	IO130RSB2	95	IO84RSB2
24	GFB0/IO146NDB3	60	IO129RSB2	96	GDC2/IO82RSB2
25	VCOMPLF	61	IO128RSB2	97	GND
26	GFA0/IO145NPB3	62	VCCIB2	98	GDB2/IO81RSB2
27	VCCPLF	63	IO125RSB2	99	GDA2/IO80RSB2
28	GFA1/IO145PPB3	64	IO123RSB2	100	GNDQ
29	GND	65	GND	101	TCK
30	GFA2/IO144PDB3	66	IO121RSB2	102	TDI
31	IO144NDB3	67	IO119RSB2	103	TMS
32	GFB2/IO143PDB3	68	IO117RSB2	104	VMV2
33	IO143NDB3	69	IO115RSB2	105	GND
34	GFC2/IO142PDB3	70	IO113RSB2	106	VPUMP
35	IO142NDB3	71	VCC	107	NC
36	NC	72	VCCIB2	108	TDO

FG144	
Pin Number	**A3P125 Function**
K1	GEB0/IO109RSB1
K2	GEA1/IO108RSB1
K3	GEA0/IO107RSB1
K4	GEA2/IO106RSB1
K5	IO100RSB1
K6	IO98RSB1
K7	GND
K8	IO73RSB1
K9	GDC2/IO72RSB1
K10	GND
K11	GDA0/IO66RSB0
K12	GDB0/IO64RSB0
L1	GND
L2	VMV1
L3	GEB2/IO105RSB1
L4	IO102RSB1
L5	VCCIB1
L6	IO95RSB1
L7	IO85RSB1
L8	IO74RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO104RSB1
M3	IO103RSB1
M4	IO101RSB1
M5	IO97RSB1
M6	IO94RSB1
M7	IO86RSB1
M8	IO75RSB1
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG484	
Pin Number	**A3P400 Function**
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3
G5	IO151UDB3
G6	GAC2/IO153UDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0

FG484	
Pin Number	**A3P400 Function**
G13	IO40RSB0
G14	IO46RSB0
G15	GNDQ
G16	IO47RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO150PDB3
H5	IO08RSB0
H6	IO153VDB3
H7	IO152VDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO65RSB1
H18	IO52RSB0
H19	IO66PDB1
H20	VCC
H21	NC
H22	NC
J1	NC
J2	NC
J3	NC
J4	IO150NDB3

FG484	
Pin Number	**A3P400 Function**
J5	IO149NPB3
J6	IO09RSB0
J7	IO152UDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO62NDB1
J17	IO49RSB0
J18	IO64PPB1
J19	IO66NDB1
J20	NC
J21	NC
J22	NC
K1	NC
K2	NC
K3	NC
K4	IO148NDB3
K5	IO148PDB3
K6	IO149PPB3
K7	GFC1/IO147PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO67PPB1
K17	IO64NPB1
K18	IO73PDB1

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3 Device Status" table on page IV, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

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The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

This version contains information that is considered to be final.

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